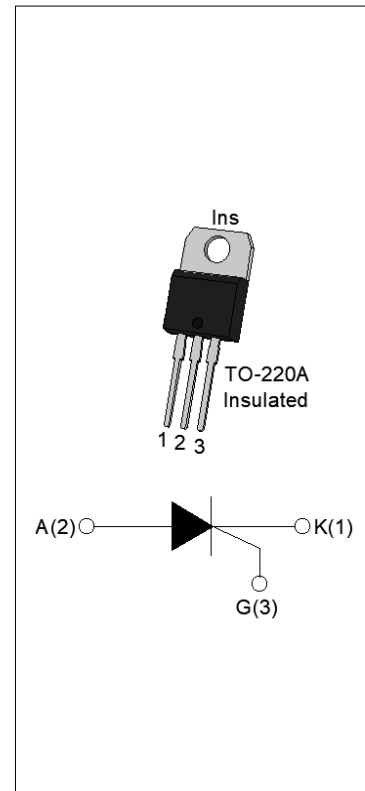




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT816A of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT816A provides a rated insulation voltage of 2500 V_{RMS} , complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	15	mA

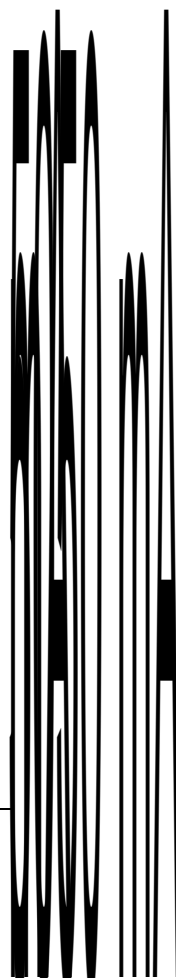
ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
Average on-state current ($T_c = 76^\circ C$)	$I_{T(AV)}$	10	A
RMS on-state current ($T_c = 76^\circ C$)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	150	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		165	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	113	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	150	$A/\mu s$

Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	5	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	60	mA



ORDERING INFORMATION

	J	CT	8	16	A
JieJie Microelectronics Co., Ltd.		SCRs			A:TO-220A(Ins)
		8:V _{DRM} /V _{RRM} 800V		I _{T(RMS)} :16A	

MARKING

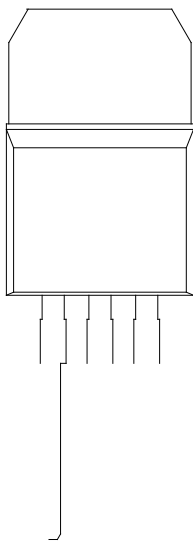


FIG.1: Maximum power dissipation versus RMS on-state current

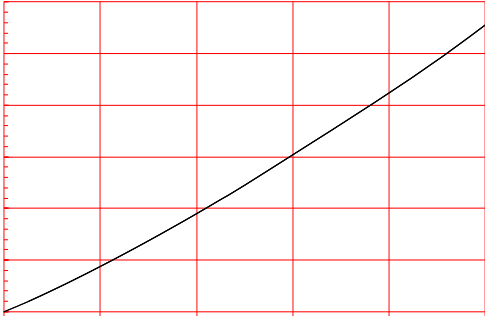


FIG.2: RMS on-state current versus case temperature

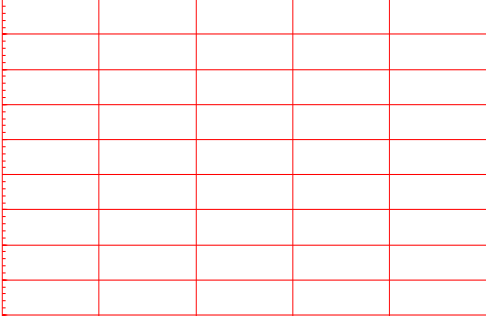
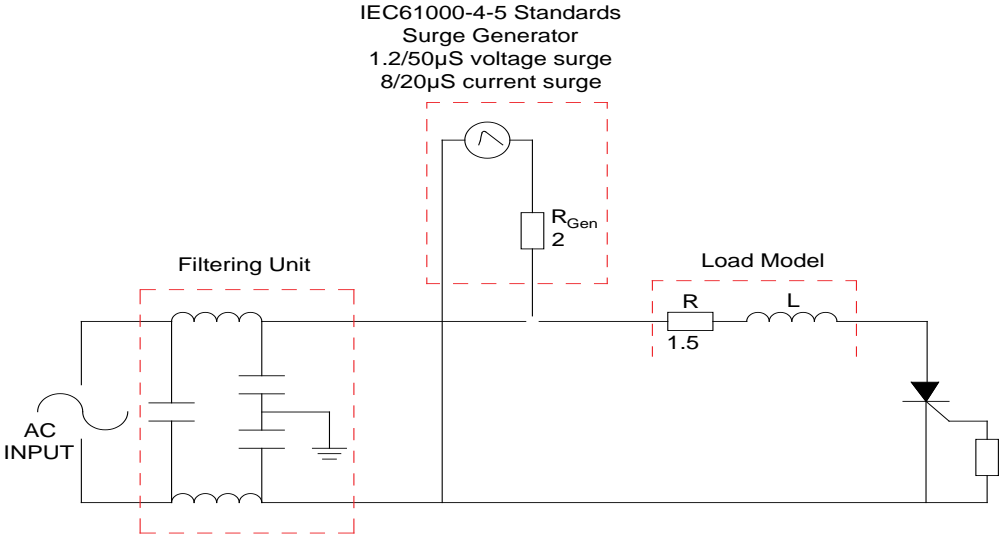


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT816A	800	15	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
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JCT816A

